

# RJK03B8DPA

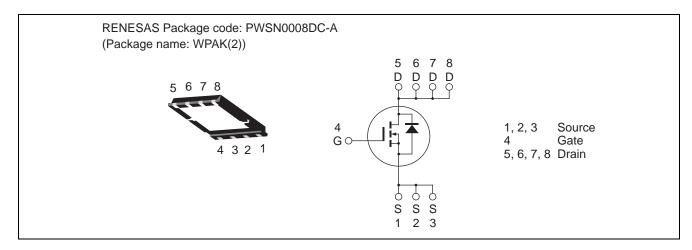
# Silicon N Channel Power MOS FET Power Switching

REJ03G1790-0210 Rev.2.10 May 12, 2010

#### **Features**

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance  $R_{DS(on)} = 7.2 \ m\Omega \ typ. \ (at \ V_{GS} = 10 \ V)$
- Pb-free
- Halogen-free

#### **Outline**



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

| Item                                   | Symbol                      | Ratings     | Unit |
|--|-----------------------------|-------------|------|
| Drain to source voltage                | V <sub>DSS</sub>            | 30          | V    |
| Gate to source voltage                 | V <sub>GSS</sub>            | ±20         | V    |
| Drain current                          | I <sub>D</sub>              | 30          | A    |
| Drain peak current                     | I <sub>D(pulse)</sub> Note1 | 120         | A    |
| Body-drain diode reverse drain current | I <sub>DR</sub>             | 30          | A    |
| Avalanche current                      | I <sub>AP</sub> Note 2      | 9           | A    |
| Avalanche energy                       | E <sub>AR</sub> Note 2      | 8.1         | mJ   |
| Channel dissipation                    | Pch Note3                   | 28          | W    |
| Channel to case thermal impedance      | θch-c Note3                 | 4.46        | °C/W |
| Channel temperature                    | Tch                         | 150         | °C   |
| Storage temperature                    | Tstg                        | -55 to +150 | °C   |

Notes: 1. PW  $\leq$  10  $\mu s, \, duty \, cycle \leq$  1%

- 2. Value at Tch = 25°C, Rg  $\geq$  50  $\Omega$
- 3. Tc = 25°C

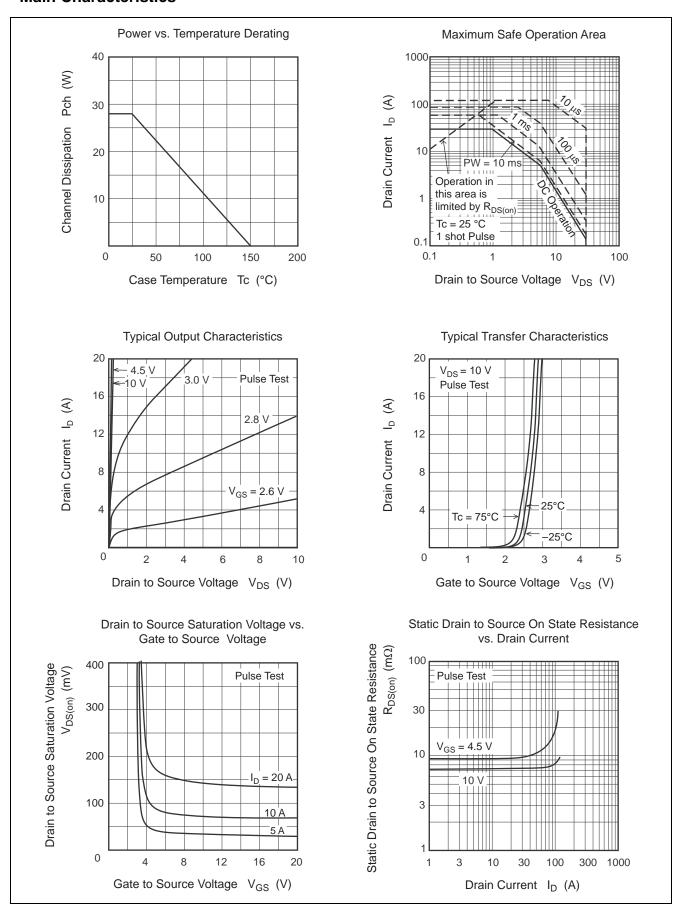
# **Electrical Characteristics**

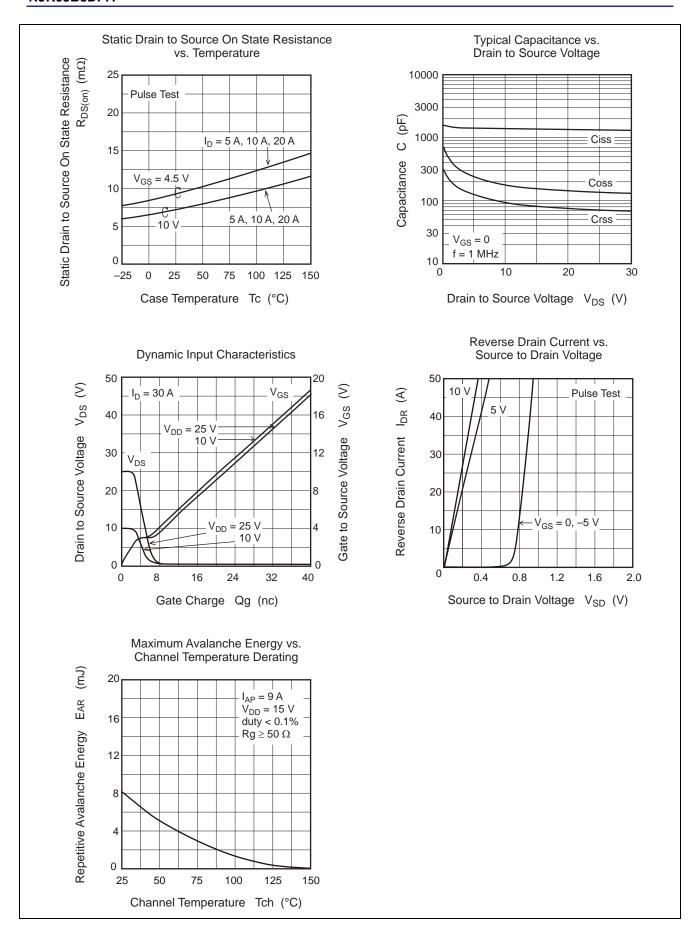
 $(Ta = 25^{\circ}C)$ 

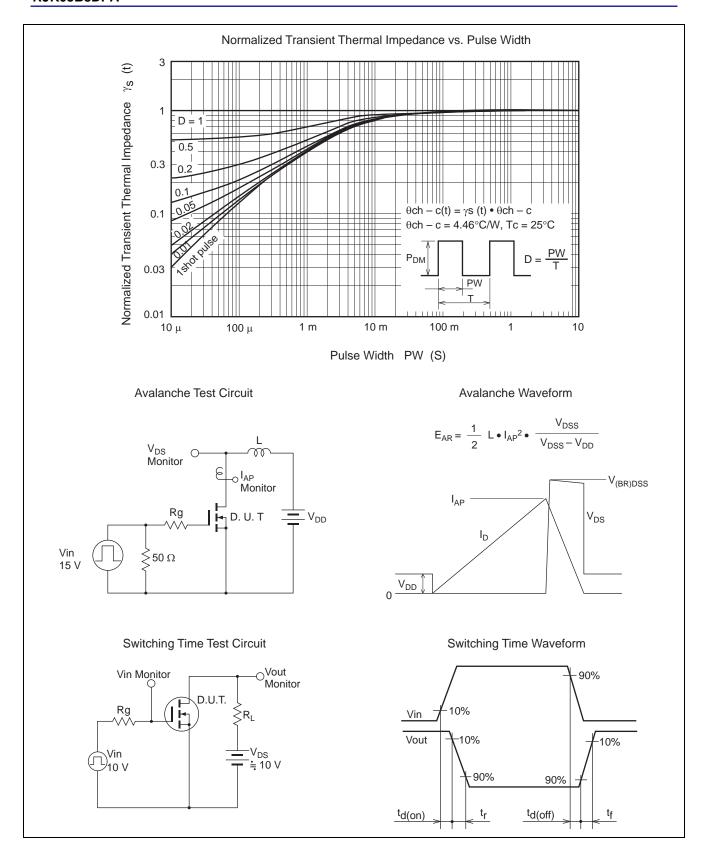
| Item                              | Symbol               | Min | Тур  | Max   | Unit | Test Conditions   |
|-----------------------------------|----------------------|-----|------|-------|------|---|
| Drain to source breakdown voltage | V <sub>(BR)DSS</sub> | 30  | _    | _     | V    | $I_D = 10 \text{ mA}, V_{GS} = 0$                           |
| Gate to source leak current       | I <sub>GSS</sub>     | _   | _    | ± 0.1 | μΑ   | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$                     |
| Zero gate voltage drain current   | I <sub>DSS</sub>     | _   | _    | 1     | μΑ   | $V_{DS} = 30 \text{ V}, V_{GS} = 0$                         |
| Gate to source cutoff voltage     | V <sub>GS(off)</sub> | 1.2 | _    | 2.5   | V    | $V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$               |
| Static drain to source on state   | R <sub>DS(on)</sub>  |     | 7.2  | 9.3   | mΩ   | $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$  |
| resistance                        | R <sub>DS(on)</sub>  |     | 9.3  | 12.9  | mΩ   | $I_D = 15 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$ |
| Forward transfer admittance       | y <sub>fs</sub>      |     | 75   | _     | S    | $I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$  |
| Input capacitance                 | Ciss                 |     | 1330 | _     | pF   | V <sub>DS</sub> = 10 V                                      |
| Output capacitance                | Coss                 |     | 185  | _     | pF   | $V_{GS} = 0$  |
| Reverse transfer capacitance      | Crss                 |     | 95   | _     | pF   | f = 1 MHz   |
| Gate Resistance                   | Rg                   |     | 1.2  | _     | Ω    |   |
| Total gate charge                 | Qg                   |     | 9    | _     | nC   | V <sub>DD</sub> = 10 V                                      |
| Gate to source charge             | Qgs                  | -   | 3.8  | _     | nC   | V <sub>GS</sub> = 4.5 V                                     |
| Gate to drain charge              | Qgd                  |     | 2.2  | _     | nC   | $I_D = 30 \text{ A}$  |
| Turn-on delay time                | t <sub>d(on)</sub>   |     | 9    | _     | ns   | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A               |
| Rise time                         | t <sub>r</sub>       |     | 4.3  | _     | ns   | $V_{DD} \cong 10 \text{ V}$                                 |
| Turn-off delay time               | t <sub>d(off)</sub>  |     | 35   | _     | ns   | $R_L = 0.67 \Omega$   |
| Fall time                         | t <sub>f</sub>       |     | 4.9  | _     | ns   | $Rg = 4.7 \Omega$   |
| Body-drain diode forward voltage  | $V_{DF}$             | _   | 0.87 | 1.14  | V    | $I_F = 30 \text{ A}, V_{GS} = 0^{\text{Note4}}$             |
| Body-drain diode reverse recovery | t <sub>rr</sub>      | _   | 14   | _     | ns   | I <sub>F</sub> =30 A, V <sub>GS</sub> = 0                   |
| time                              |                      |     |      |       |      | $di_F/dt = 100 A/ \mu s$                                    |

Notes: 4. Pulse test

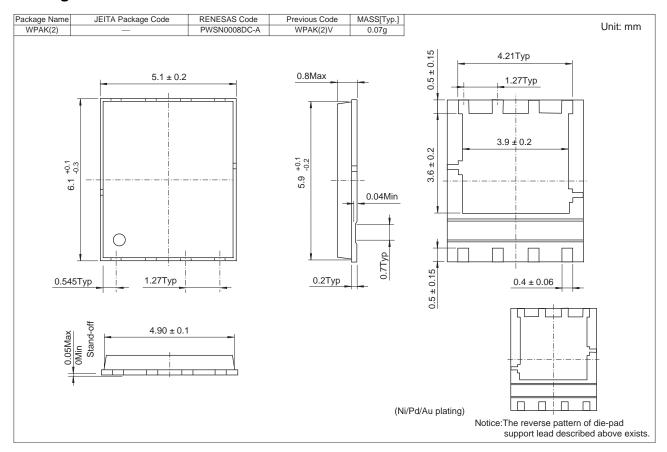
#### **Main Characteristics**







# **Package Dimensions**



# **Ordering Information**

| Part No.          | Quantity | Shipping Container |
|-------------------|----------|--------------------|
| RJK03B8DPA-00-J53 | 3000 pcs | Taping             |

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